# The RF Line NPN Silicon RF Low Power Transistor

Designed primarily for wideband large signal predriver stages in the UHF frequency range.

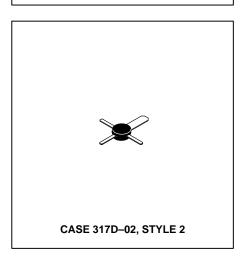
- Specified @ 12.5 V, 470 MHz Characteristics @ P<sub>out</sub> = 1.5 W Common Emitter Power Gain = 12.5 dB (Typ) Efficiency 60% (Typ)
- Cost Effective PowerMacro Package
- · Electroless Tin Plated Leads for Improved Solderability
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	16	Vdc
Collector-Base Voltage	V <sub>СВО</sub>	36	Vdc
Emitter–Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current — Continuous	IC	400	mAdc
Operating Junction Temperature	TJ	150	°C
Total Device Dissipation @ T <sub>C</sub> = 75°C (1, 2) Derate above 75°C	PD	3.0 40	Watts mW/°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

## **MRF555**

1.5 W, 470 MHz RF LOW POWER TRANSISTOR NPN SILICON



#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case		25	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	<u>.</u>		•		•
Collector–Emitter Breakdown Voltage (IC = 5.0 mAdc, IB = 0)	V(BR)CEO	16	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 5.0 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 0.1 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4.0	_	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 15 Vdc, V <sub>BE</sub> = 0, T <sub>C</sub> = 25°C)	ICES	_	_	0.1	mAdc
ON CHARACTERISTICS			•	•	•
DC Current Gain (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 5.0 Vdc)	hFE	50	90	200	_
DYNAMIC CHARACTERISTICS	<u>.</u>			•	-
Output Capacitance (V <sub>CB</sub> = 15 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	3.5	5.0	pF

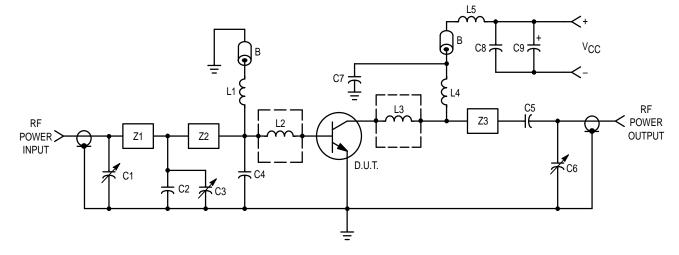
NOTES: (continued)

- 1. T<sub>C</sub>, Case temperature measured on collector lead immediately adjacent to body of package.
- The MRF555 PowerMacro must be properly mounted for reliable operation. AN938, "Mounting Techniques in PowerMacro Transistor," discusses methods of mounting and heatsinking.



**ELECTRICAL CHARACTERISTICS** — **continued** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
FUNCTIONAL TESTS (f = 470 MHz)	FUNCTIONAL TESTS (f = 470 MHz)					
Common–Emitter Power Gain (V <sub>CC</sub> = 12.5 Vdc, P <sub>Out</sub> = 1.5 W)	G <sub>pe</sub>	11	12.5	_	dB	
Collector Efficiency (V <sub>CC</sub> = 12.5 Vdc, P <sub>Out</sub> = 1.5 W)	ης	50	60	_	%	
Load Mismatch Stress (V <sub>CC</sub> = 15.5 Vdc, P <sub>in</sub> = 125 mW, VSWR ≥ 10:1 all phase angles)	Ψ	No Degradation in Output Power				



\*C1, C3, C6 — 0.8-11 pF Johanson

C2 — 15 pF Clamped Mica, Mini–Underwood

C4 — 36 pF Clamped Mica, Mini-Underwood

C5 — 470 pF Ceramic Chip Capacitor

C7 — 91 pF Clamped Mica, Mini-Underwood

C8 — 68 pF Clamped Mica, Mini-Underwood

 $C9 - 1.0 \,\mu\text{F}$ , 25 V Tantalum

B — Bead, Ferroxcube 56-590-65/3B

\*Fixed tuned for broadband response

L1 — 5 Turns #21 AWG, 5/32" I.D.

L2, L3 — 60 x 125 x 250 Mils Copper Pad on 27 Mil Thick

Alumina Substrate

L4, L5 — 7 Turns #21 AWG 5/32" I.D.

Z1 — 1.29" x 0.16" Microstrip

Z2 — 0.70" x 0.16" Microstrip Z3 — 2.18" x 0.16" Microstrip

PCB — 1/16" Glass Teflon, 1 oz. cu. clad, double sided,  $\epsilon_{\Gamma}$  = 2.5

Figure 1. 400-512 MHz Broadband Circuit

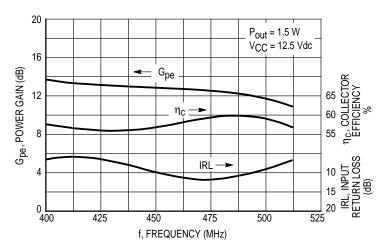
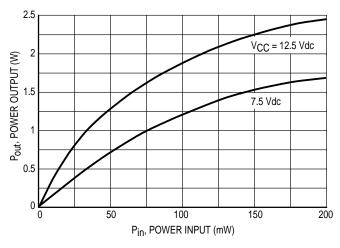


Figure 2. Performance in Broadband Circuit

	Z <sub>in</sub> Ohms		Z <sub>OL</sub> * Ohms	
	V <sub>CC</sub> = 7.5 V	V <sub>CC</sub> = 12.5 V	V <sub>CC</sub> = 7.5 V	V <sub>CC</sub> = 12.5 V
f Frequency MHz	P <sub>in</sub> = 100 mW	P <sub>in</sub> = 50 mW	P <sub>out</sub> 400 MHz = 1.5 W P <sub>out</sub> 450 MHz = 1.35 W P <sub>out</sub> 512 MHz = 1.05 W	P <sub>out</sub> 400 MHz = 1.9 W P <sub>out</sub> 450 MHz = 1.45 W P <sub>out</sub> 512 MHz = 0.9 W
400	2.9 – j2.7	1.9 – j3.1	18.0 – j13.4	12.2 – j19.7
450	2.2 – j0.8	2.6 – j4.0	21.6 = j9.9	20.2 – j18.6
512	3.5 – j1.2	2.6 – j2.6	20.1 – j1.0	23.4 – j23.0

 $Z_{OL}^*$  = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

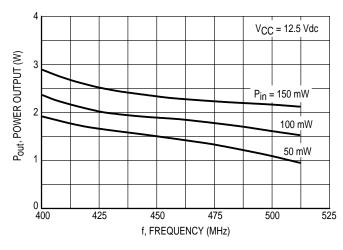
Table 1.  $Z_{\mbox{in}}$  and  $Z_{\mbox{OL}}$  versus Collector Voltage, Input Power and Output Power



2.5 (W) 100 mW 100 mW

Figure 3. Power Output versus Power Input

Figure 4. Power Output versus Frequency



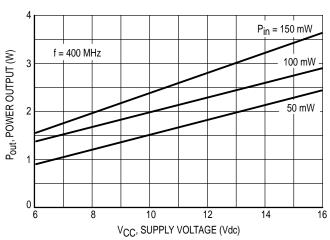
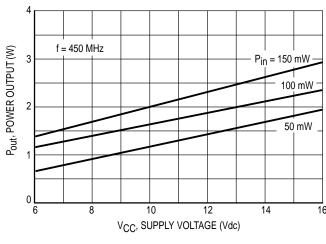


Figure 5. Power Output versus Frequency

Figure 6. Power Output versus Supply Voltage



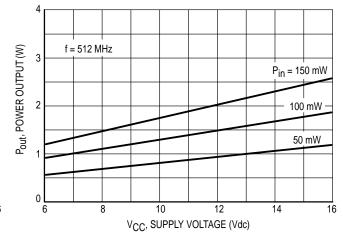
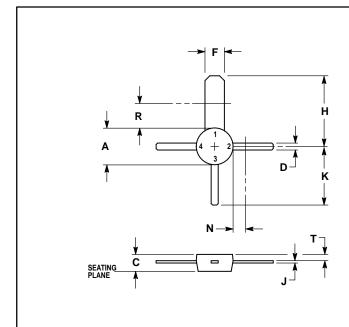


Figure 7. Power Output versus Supply Voltage

Figure 8. Power Output versus Supply Voltage

#### **PACKAGE DIMENSIONS**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION N AND R.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
С	0.075	0.100	1.91	2.54
D	0.033	0.039	0.84	0.99
F	0.097	0.104	2.46	2.64
Н	0.348	0.383	8.84	9.72
J	0.008	0.012	0.24	0.30
K	0.285	0.320	7.24	8.12
N		0.065		1.65
R		0.128		3.25
Т	0.025	0.040	0.64	1.01

STYLE 2: PIN 1. COLLECTOR 2. EMITTER 3. BASE 4. EMITTER

CASE 317D-02 ISSUE C

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